# P-Channel 60-V (D-S) MOSFET

# **Key Features:**

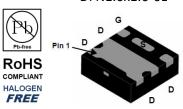
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

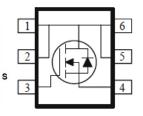
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- Load Switches
- DC/DC Conversion
- Motor Drives

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I□ (A)			
-60	200 @ V <sub>GS</sub> = -10V	-2.7			
-00	245 @ V <sub>GS</sub> = -4.5V	-2.4			

### DFN1.6x1.6-6L





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter				Limit	Units	
Drain-Source Voltage				-60	V	
Gate-Source Voltage				±20	V	
Continuous Drain Comment <sup>a</sup>		T <sub>A</sub> =25°C	. 1	-2.7		
Continuous Drain Current <sup>a</sup>	-	T <sub>A</sub> =70°C	l <sub>D</sub>	-2.4	Α	
Pulsed Drain Current <sup>b</sup>				-10		
Continuous Source Current (Diode Conduction) a	I <sub>S</sub>	-2.4	Α			
Downey Dispination 8		T <sub>A</sub> =25°C	P <sub>D</sub>	2.1	W	
Power Dissipation <sup>a</sup>	-	T <sub>A</sub> =70°C	' D	1.7	V V	
Operating Junction and Storage Temperature Range				-55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	70	°C/W			
IMAXIMUM Sunction-to-Ambient	Steady State		110	C/VV			

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### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

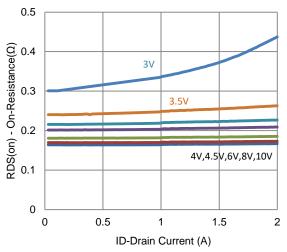
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$			-1	— uA I	
Zero Gate Voltage Brain Current	I <sub>DSS</sub>	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-4.0			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = -10 \text{ V}, I_{D} = -2 \text{ A}$			200	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -1.6 \text{ A}$			245	11122	
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -2 \text{ A}$		4		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -1.2 \text{ A}, V_{GS} = 0 \text{ V}$		-0.85		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$		4.1		nC	
Gate-Source Charge	$Q_{gs}$	$I_{D} = -2 A$		1.3			
Gate-Drain Charge	$Q_gd$	10 - 2 A		1.4			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = -30 \text{ V}, R_1 = 15 \Omega,$		5			
Rise Time	t <sub>r</sub>	$V_{DS} = -30 \text{ V}, \text{ K}_{L} = 13 \Omega,$ $I_{D} = -2 \text{ A},$		5		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		20		ns	
Fall Time	t <sub>f</sub>	VGEN = 10 V, NGEN = 0 12		7			
Input Capacitance	C <sub>iss</sub>			412			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		28		pF	
Reverse Transfer Capacitance	$C_{rss}$			22			

#### Notes

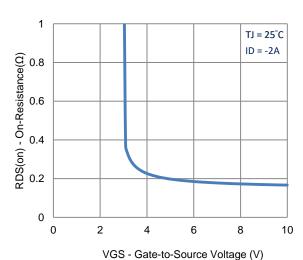
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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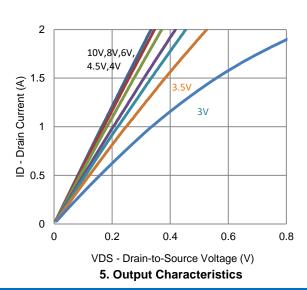
# **Typical Electrical Characteristics**



#### 1. On-Resistance vs. Drain Current

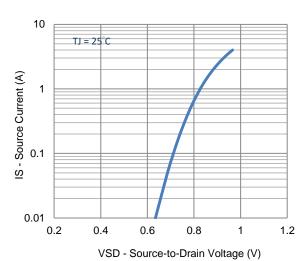


3. On-Resistance vs. Gate-to-Source Voltage

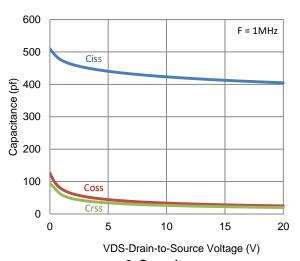


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(Y) 1.5
(Uizuno 1
0
0
1
2
3
4
5
VGS - Gate-to-Source Voltage (V)

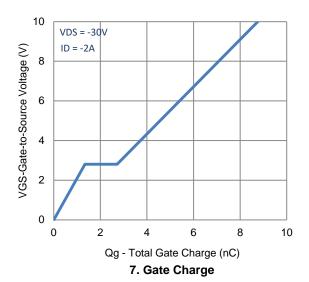
2. Transfer Characteristics

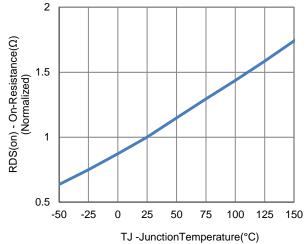


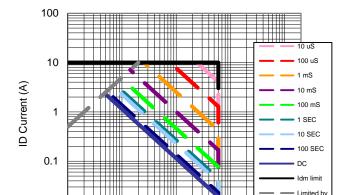
4. Drain-to-Source Forward Voltage



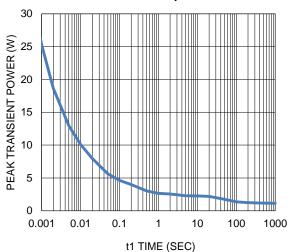
# **Typical Electrical Characteristics**







8. Normalized On-Resistance Vs Junction Temperature



VDS Drain to Source Voltage (V)

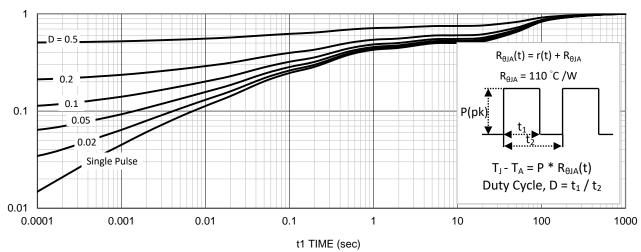
100

1000

10

9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation

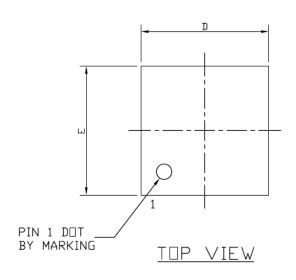


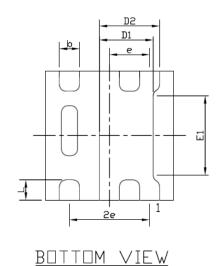
11. Normalized Thermal Transient Junction to Ambient

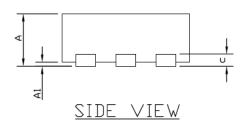
0.01

0.1

# Package Information







SYMBOLS	DIMENS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
21MBUL2	MIN	NDM	MAX	MIN	MAX			
Α	0.50	0.55	0.60	0.020	0.022	0.024		
A1	0.00		0.05	0.000		0.002		
b	0.22	0.25	0.28	0.009	0.010	0.011		
С		0.152 Ref.			0,006 Ref.			
D	1.55	1.60	1.65	0.061	0.063	0.065		
D1	0.67 TYP			0.026 TYP				
D2	0.75 TYP			0.030 TYP				
E	1.55	1.60	1.65	0.061	0.063	0.065		
E1	0.98 TYP			0.039 TYP				
е		0.50 BSC			0.020 BSC			
L	0.20	0.25	0.30	0.008	0.010	0.012		